		General Marit	e e	Time stamp
L	Hits	Search Text	: 5	12me Seamp
Number	1 210	"electrically isolated electrode"	USPAT;	2002/08/21
: -	319	melectrically isolated electrode	US-PGPUB	08:19
	122	(etch\$3 near3 backside) and conduct\$3 and	USPAT;	2002/08/22
; -	423	insulat\$3	US-PGPUB	09:22
	51	1 1 1 2 2	USPAT;	2002/08/22
1 -	71	insulat\$3 and trench and sidewall	US-PGPUB	10:33
	101	(etch\$3 near3 backside) and conduct\$3 and	USPAT;	2002/08/26
. =	101	insulat\$3 and (trench or channel or	US-PGPUB	14:59
	:	groove or via or hole) and sidewall		
	377	(etch\$3 near3 backside) and conduct\$3 and	USPAT;	12002/08/03
	1	insulat\$3 and (trench or channel or	US-PGPUB	10:56
1	I	groove or via or hole)	İ	i
_	197		USPAT;	2002/08/23
İ	1		US-PGPUB	07:57
	743	MEMS and etch\$3 and conduct\$3 and	USPAT;	2002/08/36
İ		insulat\$3 and(trench or groove or via or	US-PGPUB	14:57
		hole or channel)		
-	3709	isolated near3 (electrode or conduct\$3)	USPAT;	2002/08/23
1	1	and etch\$3	US-PGPUB	12:33
-	775	MEMS and etch\$3 and conduct\$3 and	USPAT;	2002/08/33
İ		insulat\$3 and(trench or cavity or groove	US-PGPUB	14:51
i		or via or hole or channel)		2200/00/25
-	8	(silicon adj "110") same trench and etch	USPAT;	2002/08/26
	İ		US-PGPUB	09:53
-	6229		JPO;	2000/08/06   15:08
1		(trench or channel or groove or via or	DERWENT	15:08
1	1	hole or cavity)	JPO;	2002/08/26
-	1	etch\$3 and conduct\$3 and insulat\$3 and	DERWENT	15:03
		(trench or channel or groove or via or	DELMENT	1
i		hole or cavity) and MEMS etch\$3 and conduct\$3 and insulat\$3 and	JPO;	200.1/08/37
-	598		DERWENT	10:43
	1	trench	JPC;	2002/08/27
-	12	etch\$3 and trench and (microelectromechanical or MEMS)	DEPWENT	10:44
!	1	(wiclosfectiomecuanical of Migha)		ud filati